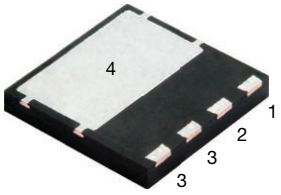
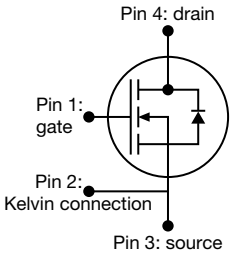
# E Series Power MOSFET

PowerPAK® 8 x 8




N-Channel MOSFET

## FEATURES

- 4th generation E series technology
- Low figure-of-merit (FOM) $R_{on}$ x $Q_g$
- Low effective capacitance ($C_{o(er)}$)
- Reduced switching and conduction losses
- Avalanche energy rated (UIS)
- Kelvin connection for reduced gate noise
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE
GREEN (5-2008)

## APPLICATIONS

- Server and telecom power supplies
- Switch mode power supplies (SMPS)
- Power factor correction power supplies (PFC)
- Lighting
  - High-intensity discharge (HID)
  - Fluorescent ballast lighting
- Industrial
  - Welding
  - Induction heating
  - Motor drives
  - Battery chargers
  - Solar (PV inverters)

| PRODUCT SUMMARY | | |
|---|---|---|
| $V_{DS}$ (V) at $T_J$ max. | 700 | |
| $R_{DS(on)}$ typ. (Ω) at 25 °C | $V_{GS}$ = 10 V | 0.106 |
| $Q_g$ max. (nC) | 57 | |
| $Q_{gs}$ (nC) | 15 | |
| $Q_{gd}$ (nC) | 14 | |
| Configuration | Single | |

| ORDERING INFORMATION | |
|---|---|
| Package | PowerPAK 8 x 8 |
| Lead (Pb)-free and halogen-free | SiHH125N65E-T1-GE3 |

| ABSOLUTE MAXIMUM RATINGS ($T_C$ = 25 °C, unless otherwise noted) | | | | | |
|---|---|---|---|---|---|
| PARAMETER | | | SYMBOL | LIMIT | UNIT |
| Drain-source voltage | | | $V_{DS}$ | 650 | V |
| Gate-source voltage | | | $V_{GS}$ | ± 30 | |
| Continuous drain current ($T_J$ = 150 °C) | $V_{GS}$ at 10 V | $T_C$ = 25 °C | $I_D$ | 25 | A |
| | | $T_C$ = 100 °C | | 16 | |
| Pulsed drain current [a] | | | $I_{DM}$ | 60 | |
| Linear derating factor | | | | 1.38 | W/°C |
| Single pulse avalanche energy [b] | | | $E_{AS}$ | 81 | mJ |
| Maximum power dissipation | | | $P_D$ | 174 | W |
| Operating junction and storage temperature range | | | $T_J$, $T_{stg}$ | -55 to +150 | °C |
| Drain-source voltage slope | | | dv/dt | 100 | V/ns |
| Reverse diode dv/dt [c] | | | | 7.1 | |

**Notes**

a. Repetitive rating; pulse width limited by maximum junction temperature
b. $V_{DD}$ = 140 V, starting $T_J$ = 25 °C, L = 28.2 mH, $R_g$ = 25 Ω, $I_{AS}$ = 2.4 A
c. $I_{SD} \leq I_D$, di/dt = 100 A/µs, starting $T_J$ = 25 °C



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| THERMAL RESISTANCE RATINGS | | | | |
|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TYP.** | **MAX.** | **UNIT** |
| Maximum junction-to-ambient | $R_{thJA}$ | 40 | 42 | °C/W |
| Maximum junction-to-case (drain) | $R_{thJC}$ | 0.55 | 0.72 | |

| SPECIFICATIONS ($T_J$ = 25 °C, unless otherwise noted) | | | | | | |
|---|---|---|---|---|---|---|
| **PARAMETER** | **SYMBOL** | **TEST CONDITIONS** | **MIN.** | **TYP.** | **MAX.** | **UNIT** |
| **Static** | | | | | | |
| Drain-source breakdown voltage | $V_{DS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 µA | 650 | - | - | V |
| $V_{DS}$ temperature coefficient | $\Delta V_{DS}/T_J$ | Reference to 25 °C, $I_D$ = 1 mA | - | 0.61 | - | V/°C |
| Gate-source threshold voltage (N) | $V_{GS(th)}$ | $V_{DS}$ = $V_{GS}$, $I_D$ = 250 µA | 3.0 | - | 5.0 | V |
| Gate-source leakage | $I_{GSS}$ | $V_{GS}$ = ± 20 V | - | - | ± 100 | nA |
| | | $V_{GS}$ = ± 30 V | - | - | ± 1 | µA |
| Zero gate voltage drain current | $I_{DSS}$ | $V_{DS}$ = 650 V, $V_{GS}$ = 0 V | - | - | 1 | µA |
| | | $V_{DS}$ = 520 V, $V_{GS}$ = 0 V, $T_J$ = 125 °C | - | - | 10 | |
| Drain-source on-state resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V, $I_D$ = 12 A | - | 0.106 | 0.120 | Ω |
| Forward transconductance [a] | $g_{fs}$ | $V_{DS}$ = 8 V, $I_D$ = 12 A | - | 11 | - | S |
| **Dynamic** | | | | | | |
| Input capacitance | $C_{iss}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 100 V, f = 100 kHz | - | 1938 | - | pF |
| Output capacitance | $C_{oss}$ | | - | 71 | - | |
| Reverse transfer capacitance | $C_{rss}$ | | - | 2 | - | |
| Effective output capacitance, energy related [a] | $C_{o(er)}$ | $V_{DS}$ = 0 V to 400 V, $V_{GS}$ = 0 V | - | 81 | - | |
| Effective output capacitance, time related [b] | $C_{o(tr)}$ | | - | 546 | - | |
| Total gate charge | $Q_g$ | $V_{GS}$ = 10 V; $I_D$ = 12 A, $V_{DS}$ = 520 V | - | 38 | 57 | nC |
| Gate-source charge | $Q_{gs}$ | | - | 15 | - | |
| Gate-drain charge | $Q_{gd}$ | | - | 14 | - | |
| Turn-on delay time | $t_{d(on)}$ | $V_{DD}$ = 520 V, $I_D$ = 12 A, $V_{GS}$ = 10 V, $R_g$ = 9.1 Ω | - | 26 | 52 | ns |
| Rise time | $t_r$ | | - | 59 | 118 | |
| Turn-off delay time | $t_{d(off)}$ | | - | 46 | 92 | |
| Fall time | $t_f$ | | - | 26 | 52 | |
| Gate input resistance | $R_g$ | f = 1 MHz | 0.4 | 0.8 | 1.6 | Ω |
| **Drain-Source Body Diode Characteristics** | | | | | | |
| Continuous source-drain diode current | $I_S$ | MOSFET symbol showing the integral reverse p - n junction diode  | - | - | 25 | A |
| Pulsed diode forward current | $I_{SM}$ | | - | - | 60 | |
| Diode forward voltage | $V_{SD}$ | $T_J$ = 25 °C, $I_S$ = 12 A, $V_{GS}$ = 0 V | - | - | 1.2 | V |
| Reverse recovery time | $t_{rr}$ | $T_J$ = 25 °C, $I_F$ = $I_S$ = 12 A, di/dt = 100 A/µs, $V_R$ = 25 V | - | 345 | 690 | ns |
| Reverse recovery charge | $Q_{rr}$ | | - | 4.4 | 8.8 | µC |
| Reverse recovery current | $I_{RRM}$ | | - | 22 | - | A |


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**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

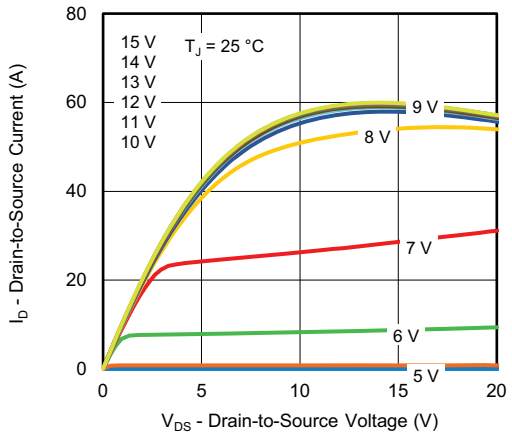


**Fig. 1 - Typical Output Characteristics**

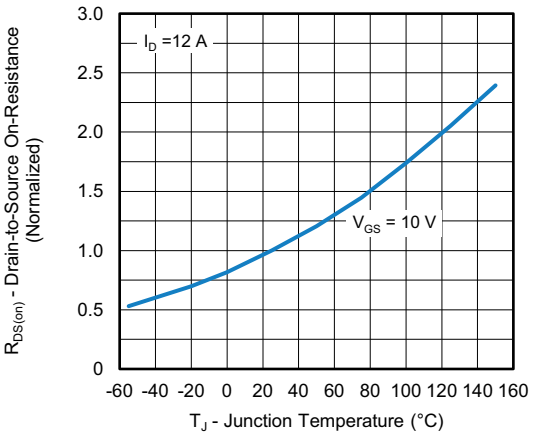


**Fig. 4 - Normalized On-Resistance vs. Temperature**

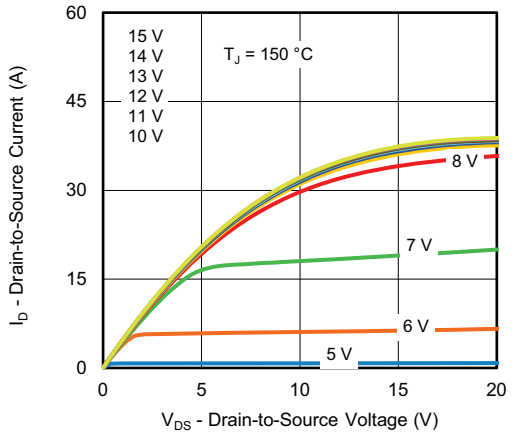


**Fig. 2 - Typical Output Characteristics**

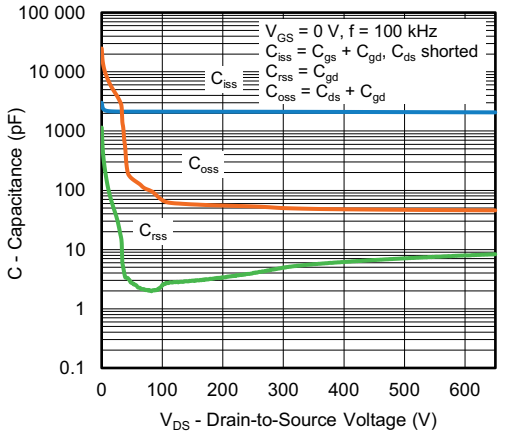


**Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage**

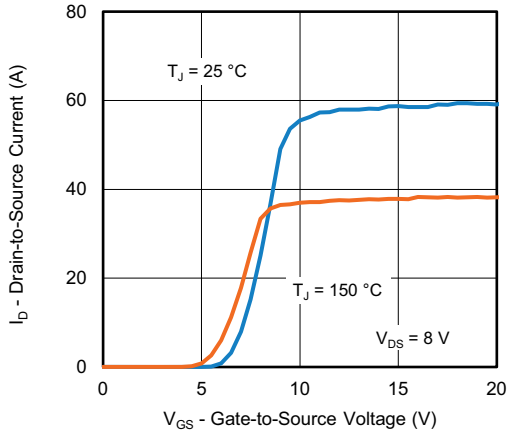


**Fig. 3 - Typical Transfer Characteristics**

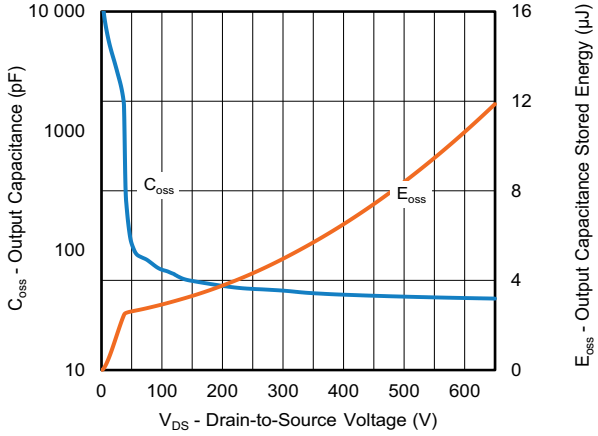


**Fig. 6 - $C_{oss}$ and $E_{oss}$ vs. $V_{DS}$**


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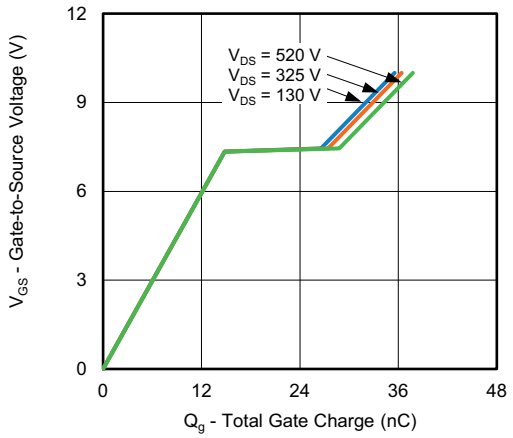


**Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage**

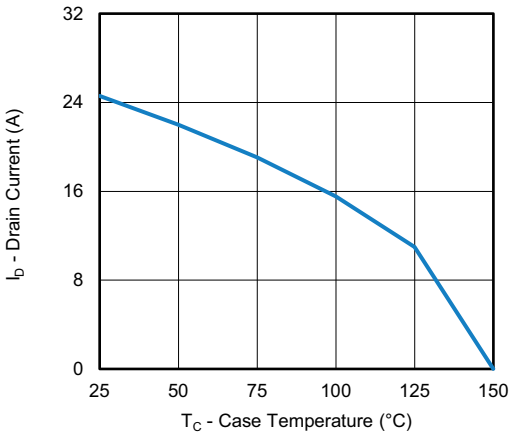


**Fig. 10 - Maximum Drain Current vs. Case Temperature**

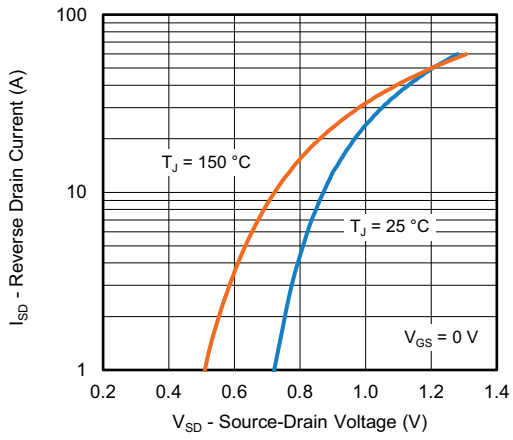


**Fig. 8 - Typical Source-Drain Diode Forward Voltage**

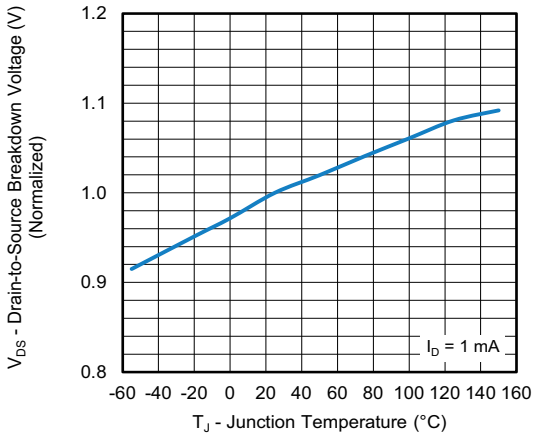


**Fig. 11 - Temperature vs. Drain-to-Source Voltage**

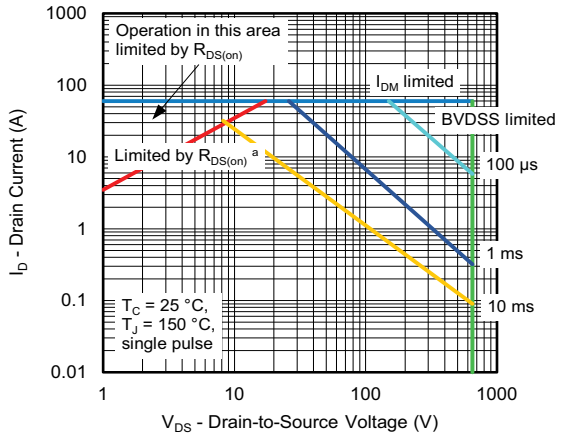


**Fig. 9 - Maximum Safe Operating Area**

**Note**

a. $V_{GS}$ > minimum $V_{GS}$ at which $R_{DS(on)}$ is specified


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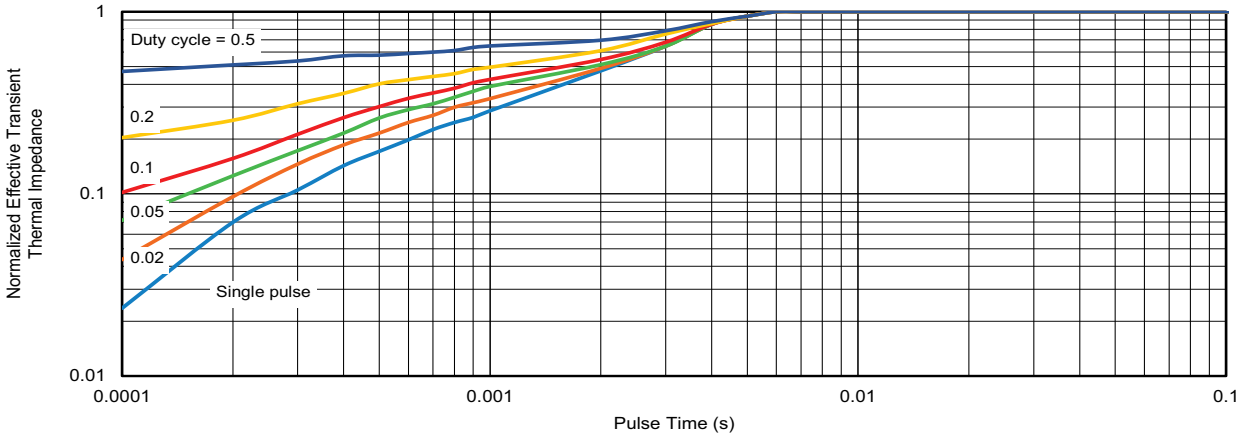


**Fig. 12 - Normalized Transient Thermal Impedance, Junction-to-Case**

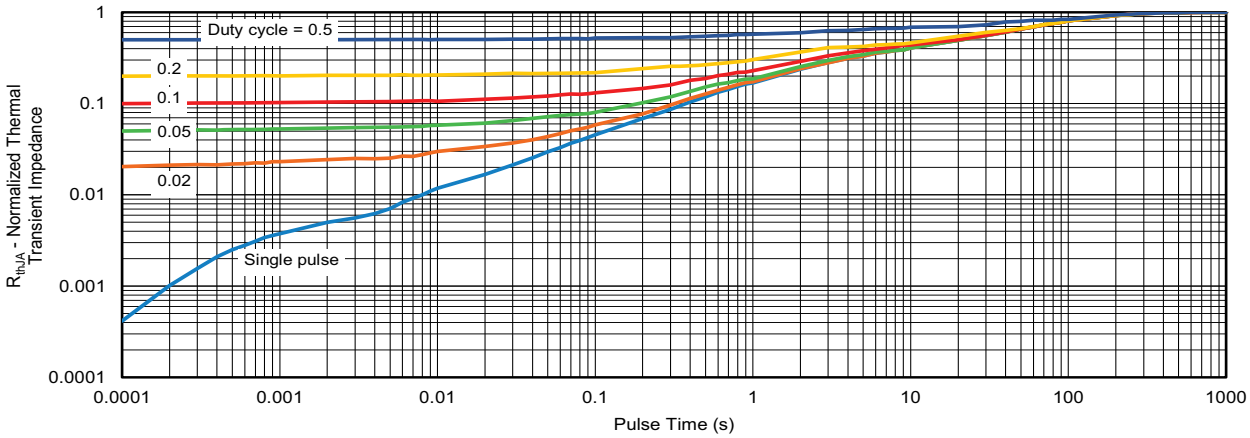


**Fig. 13 - Normalized Thermal Transient Impedance, Junction-to-Ambient**

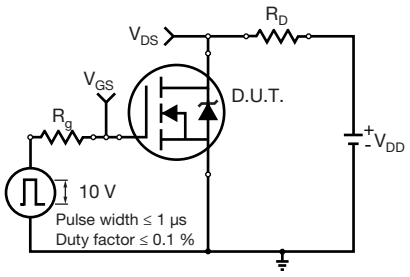


**Fig. 14 - Switching Time Test Circuit**

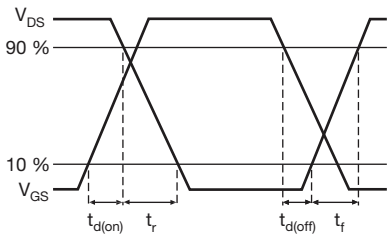


**Fig. 15 - Switching Time Waveforms**


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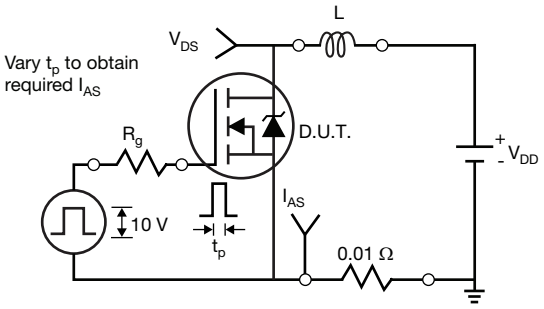


**Fig. 16 - Unclamped Inductive Test Circuit**

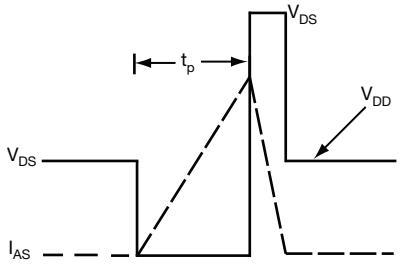


**Fig. 17 - Unclamped Inductive Waveforms**

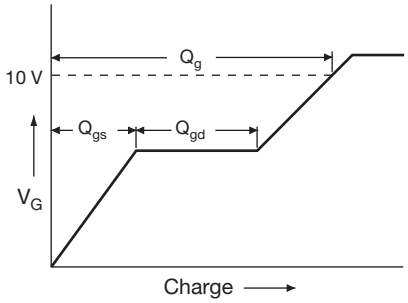


**Fig. 18 - Basic Gate Charge Waveform**

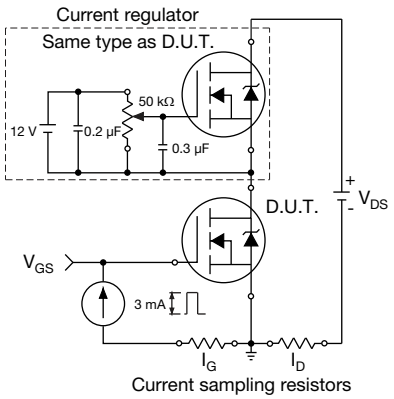


**Fig. 19 - Gate Charge Test Circuit**


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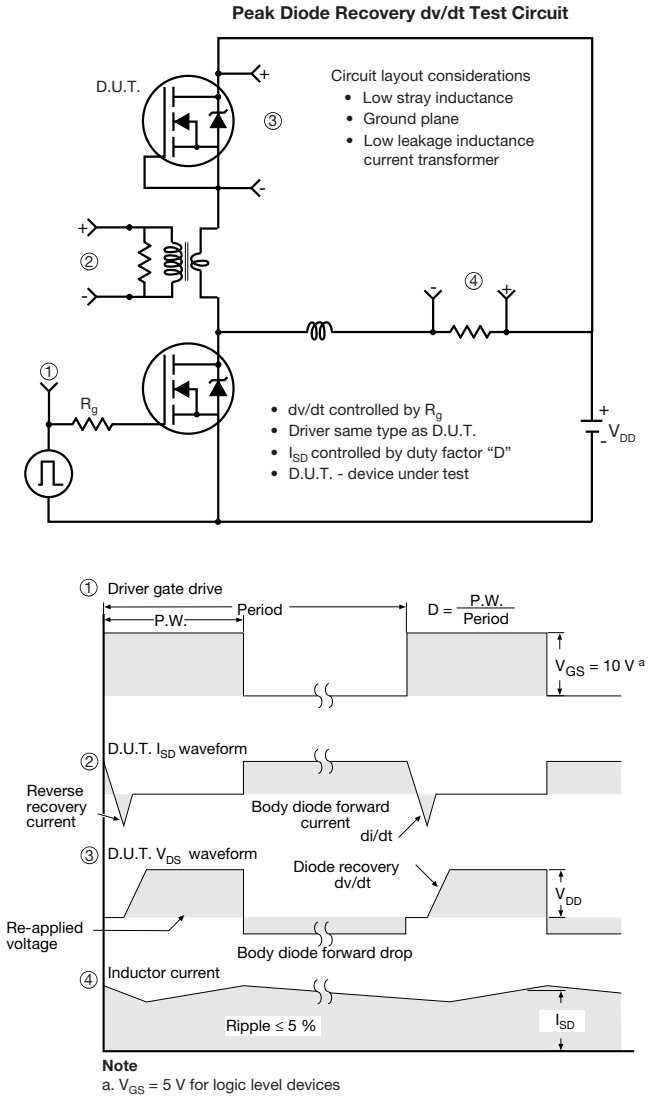


**Note**

a. $V_{GS}$ = 5 V for logic level devices

**Fig. 20 - For N-Channel**

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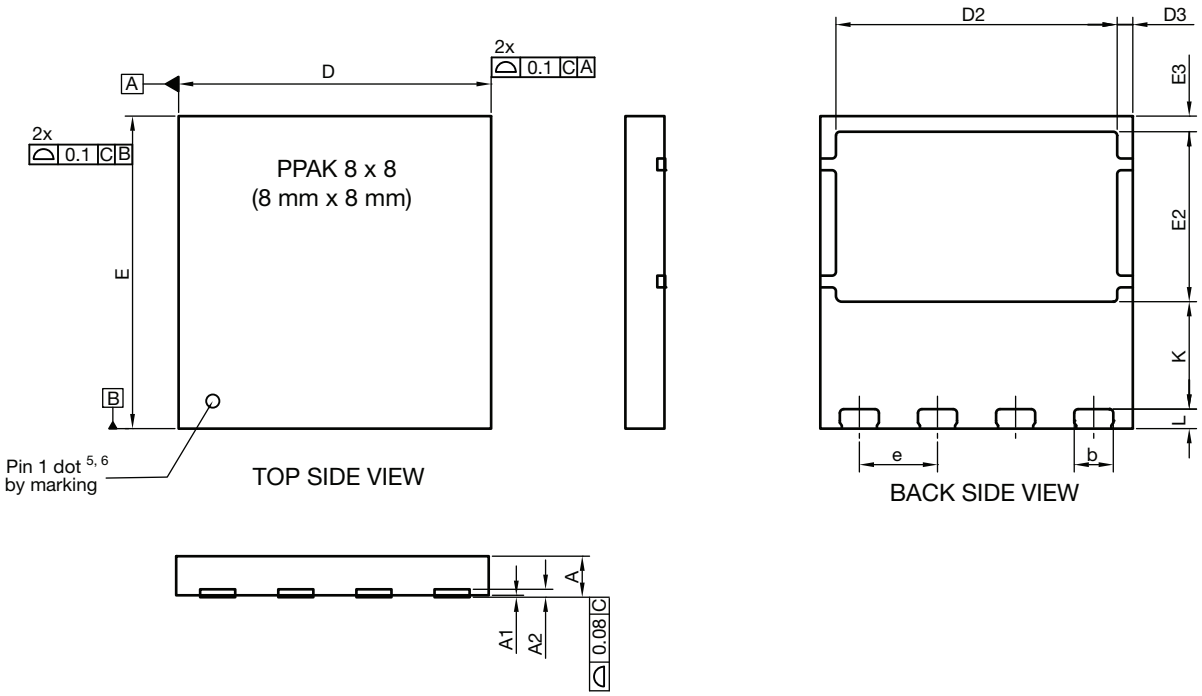
# PowerPAK® 8 x 8 Case Outline




| DIM. | MILLIMETERS | | | INCHES | | |
|---|---|---|---|---|---|---|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 |
| A1 | 0.00 | - | 0.05 | 0.000 | - | 0.002 |
| A2 | 020 ref. | | | 0.008 ref. | | |
| b | 0.95 | 1.00 | 1.05 | 0.037 | 0.039 | 0.041 |
| D | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| D2 | 7.10 | 7.20 | 7.30 | 0.280 | 0.283 | 0.287 |
| D3 | 0.40 BSC | | | 0.016 BSC | | |
| e | 2.00 BSC | | | 0.079 BSC | | |
| E | 7.90 | 8.00 | 8.10 | 0.311 | 0.315 | 0.319 |
| E2 | 4.30 | 4.35 | 4.40 | 0.169 | 0.171 | 0.173 |
| E3 | 0.40 BSC | | | 0.016 BSC | | |
| K | 2.75 BSC | | | 0.108 BSC | | |
| L | 0.45 | 0.50 | 0.55 | 0.018 | 0.020 | 0.022 |
| N (3) | 8 | | | 8 | | |

**Notes**

(1) Use millimeters as the primary measurement
(2) Dimensioning and tolerances conform to ASME Y14.5 M - 1994
(3) N is the number of terminals
(4) The pin 1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
(5) Exact shape and size of this feature is optional

ECN: E20-0518-Rev. B, 28-Sep-2020
DWG: 6041



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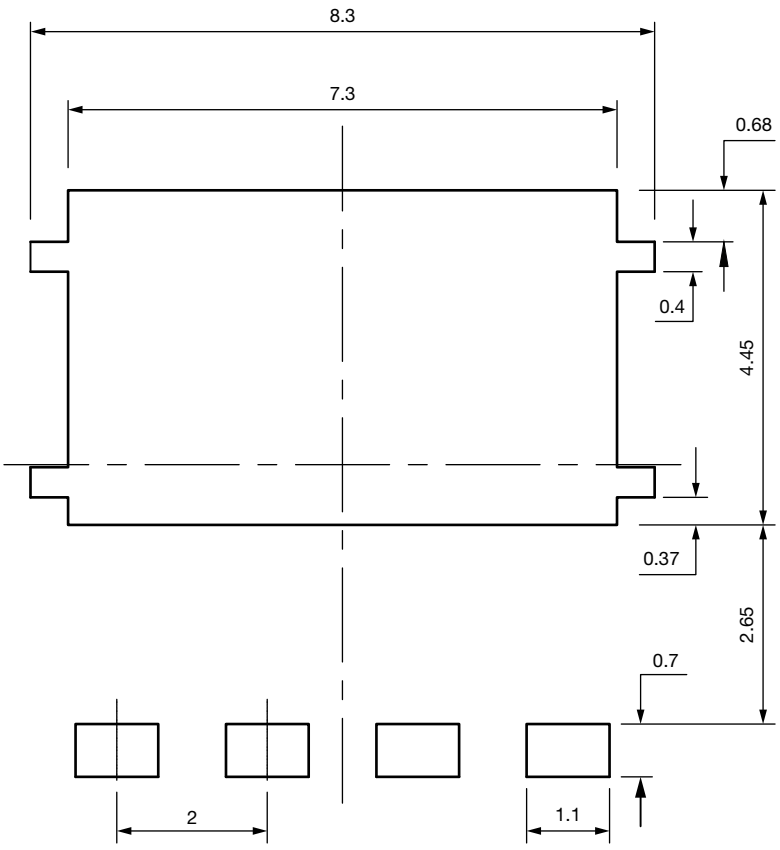
# Recommended Minimum PADs for PowerPAK® 8 mm x 8 mm




Dimensions in millimeters



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